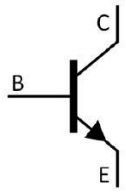
## WR0<5 ṂṂ Ḅ QSQ ÆṀ ч s ‖ ㄱ Silicon NPN transistor in a TO-92 Plastic Package.

## ш ` ㄡ/kıн ㄔ ớ Ḅ

High gain, good linearity of $h_{FE}$.

## ₹ ↄ ð ㄱ g ɛ ѽ ᶻ

TV final picture IF amplifier applications.

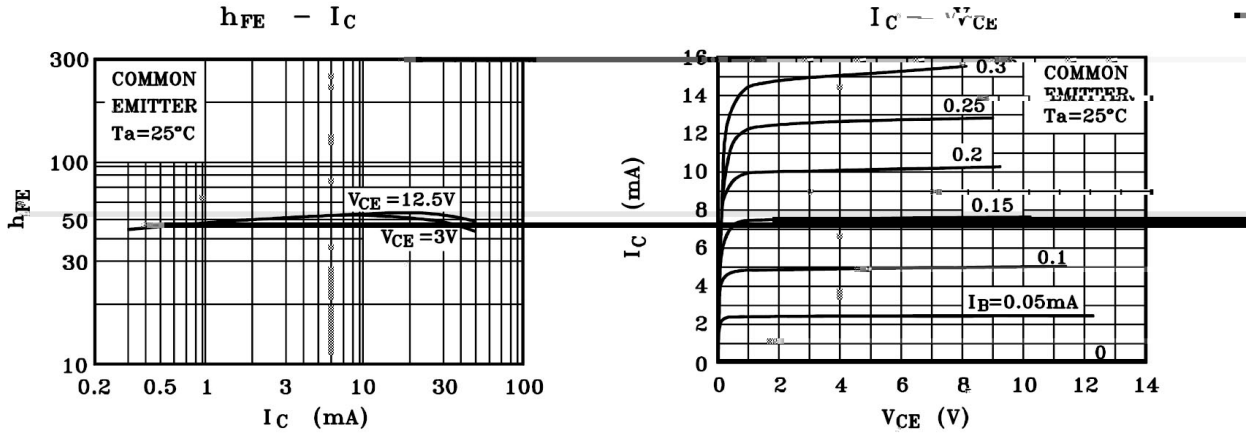


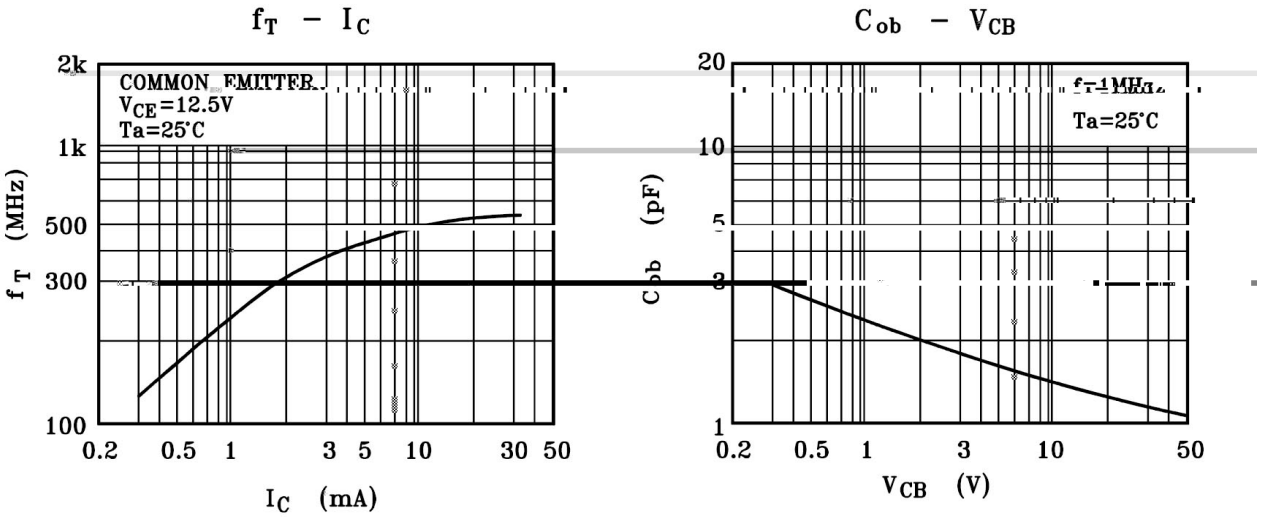
PIN1 χ Collector PIN 2 χ Emitter PIN 3 χ Base

## ð м ㄚ ب ˝ See Marking Instructions.

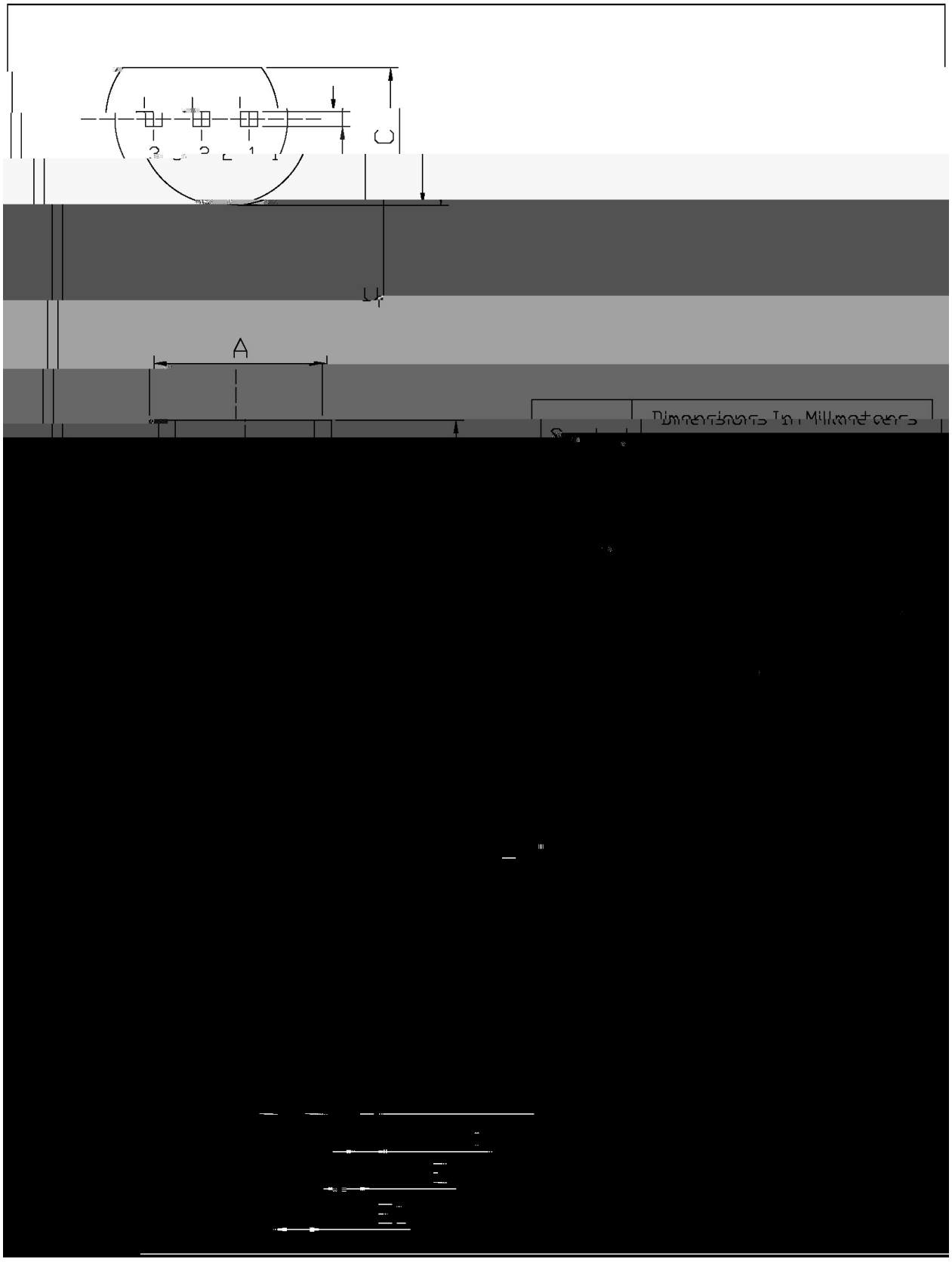
| v ̈Ọ<br>Parameter | ϒ N<br>Symbol | ̈Ọ Ö<br>Rating | D Ꮋ<br>Unit |
|---|---|---|---|
| Collector to Base Voltage | $V_{CBO}$ | 30 | V |
| Collector to Emitter Voltage | $V_{CEO}$ | 25 | V |
| Emitter to Base Voltage | $V_{EBO}$ | 4.0 | V |
| Collector Current - Continuous | $I_C$ | 50 | mA |
| Emitter Current - Continuous | $I_E$ | -50 | mA |
| Collector Power Dissipation | $P_C$ | 300 | mW |
| Junction Temperature | $T_j$ | 150 | |
| Storage Temperature Range | $T_{stg}$ | -55 150 | |

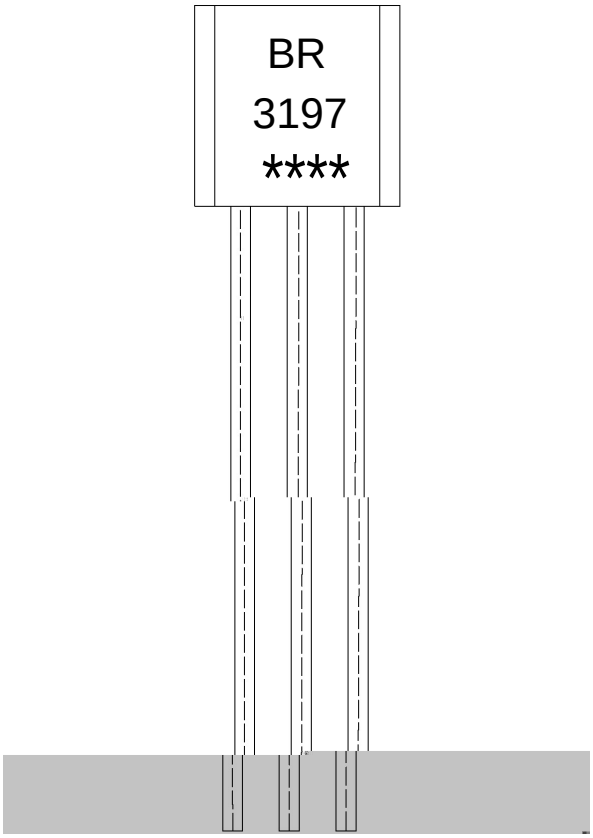
| v ̈Ọ<br>Parameter | ϒ N<br>Symbol | ᗻ ; ʃ Ţ<br>Test Conditions | ѡ ṇ Ö<br>Min | Ɛ ʒ Ö<br>Typ | ѡ ᶻ Ö<br>Max | D Ꮋ<br>Unit |
|---|---|---|---|---|---|---|
| Collector to Emitter Breakdown Voltage | $V_{CEO}$ | $I_C$=10mA $I_B$=0 | 25 | | | V |


$h_{FE}$ – $I_C$
COMMON EMITTER
Ta=25°C
$V_{CE}$ =12.5V
$V_{CE}$ =3V
$h_{FE}$
$I_C$ (mA)
$I_C$ – $V_{CE}$
COMMON EMITTER
Ta=25°C
0.3
0.25
0.2
0.15
0.1
$I_B$=0.05mA
0
$I_C$ (mA)
$V_{CE}$ (V)


$f_T$ – $I_C$
COMMON EMITTER
$V_{CE}$=12.5V
Ta=25°C
$f_T$ (MHz)
$I_C$ (mA)
$C_{ob}$ – $V_{CB}$
Ta=25°C
$C_{ob}$ (pF)
$V_{CB}$ (V)

TO-92 Unit: mm



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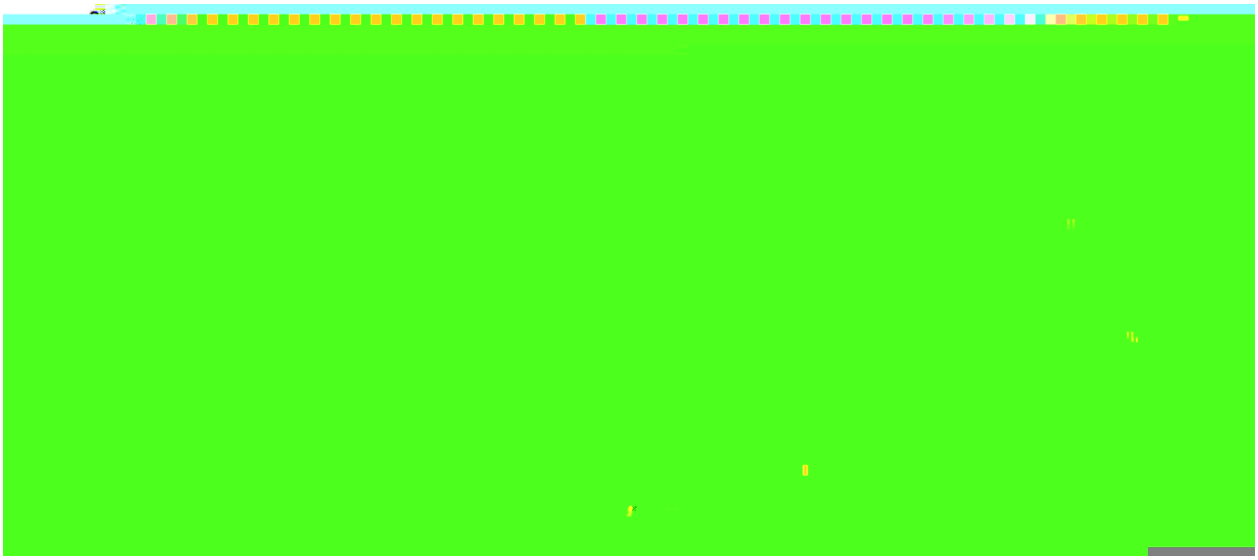
Note:

BR: Company Code.

3197: Product Type.

****: Lot No. Code,code change with Lot No.



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı `H ڑ `Y ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﻉ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

□ ỷ χ 270 ° 5 ł `H ڑ χ 10 ° 1 sec. Temp:270±5 Time:10±1 sec

`Ọ ţ ﾔ Ł / BULK